

PATENT

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ABSTRACT OF THE DISCLOSURE

A semiconductor device having contact surfaces of different heights electrically connected to conductors defined on one or more patterned metal planes and a method for fabricating the semiconductor device. In one embodiment, the semiconductor device comprises a substrate having a process surface; a first contact and a second contact arranged on the substrate, a second contact surface of the second contact being at a greater distance, in a substrate-normal direction, from the substrate than a first contact surface of the first contact; a first conductor disposed in a first patterned metal plane and electrically connected to the first contact surface; and a second conductor disposed in a second patterned metal plane and electrically connected to the second contact surface, wherein the second metal plane is disposed at a greater distance, in the substrate-normal direction, from the substrate than the first metal plane.